

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	11	(first second) adj ((buried adj strap) or buriedstrap)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/05/04 08:27
L2	2961	((365/149) or (365/131) or (257/220)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/04 08:21
L3	1	1 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/05/04 08:21
L4	1071	((buried adj strap) or buriedstrap)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/05/04 08:22
L5	27	2 4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/05/04 08:22
L6	6	((first second) adj ((buried adj strap) or buriedstrap)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/05/04 08:26
L7	1313	(257/301).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/04 08:26
L8	213	4 7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/05/04 08:27

EAST Search History

L9	117	4 7 voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/05/04 08:27
L10	56	4 7 (threshold adj voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/05/04 08:27
L11	6	4 7 (threshold adj voltage) (pass adj transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/05/04 08:27
L14	657	(365/185.24).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/04 08:41
L15	1	4 14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/05/04 08:41
S1	1	Gate adj controlled adj floating adj well	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/05/04 08:20
S2	9	("20050190590" "20030116792" "20030155609" "5455801" "20030224573" "6269280" "20030082876" "6534824" "4713678").pn.	US-PGPUB; USPAT	OR	ON	2005/11/21 09:52
S3	116899	DRAM	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/21 16:50

EAST Search History

S4	981	deep adj trench adj capacitor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/21 16:50
S5	785	S3 S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/21 16:50
S6	43	vertical adj pass adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/21 16:50
S7	8	S5 S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/21 16:52
S8	8	S5 S6 control	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/21 16:53
S9	13	second adj buried adj strap	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/21 17:34
S10	1	S9 S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/21 16:53
S11	2585	(365/149).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/21 17:35

EAST Search History

S12	192	S11 (control adj gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/21 17:36
S13	112	S11 (control adj gate) (DRAM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/21 17:36
S14	98	S11 (control adj gate) (DRAM) (source drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/21 17:36
S15	90	S11 (control adj gate) (DRAM) (source drain) (capacitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/21 17:36
S16	2	S11 (control adj gate) (DRAM) (source drain) (deep adj2 capacitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/21 17:37
S17	16	S11 (control adj gate) (DRAM) (source drain) (trench adj capacitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/21 17:58
S18	123	(trench adj capacitor) ((word or floating) adj gate) (control adj gate) DRAM	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/21 18:39
S19	35	(trench adj capacitor) ((word or floating) adj gate) (control adj gate) (vertical adj2 transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/21 18:36

EAST Search History

S20	8	(control adj cell) (trench adj capacitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/21 18:32
S21	2	"20050133860"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/21 18:32
S22	2	("08/792952" or "08/787419").app.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/21 18:37
S23	14	(trench adj capacitor) ((word or floating) adj gate) (control adj gate) DRAM (buried adj strap)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/21 18:42
S24	10	(trench adj capacitor) ((word or floating) adj gate) (control adj gate) DRAM (buried adj strap) (threshold adj voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 07:59
S25	90	"6072209"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 09:06
S26	463	(control adj cell) (storage adj cell)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 10:30
S29	2	(control adj cell) (storage adj cell) (trench adj5 capacitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 09:07

EAST Search History

S30	3	(control adj cell) (storage adj cell) (vertical adj3 transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 09:07
S31	981	(vertical adj3 transistor) (trench adj3 capacitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 10:34
S32	873	(vertical adj3 transistor) (trench adj3 capacitor) (DRAM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 10:34
S33	314	(vertical adj3 transistor) (trench adj3 capacitor) (DRAM) (buried adj strap)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 10:34
S34	86	(vertical adj3 transistor) (trench adj3 capacitor) (DRAM) (buried adj strap) (threshold adj voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:06
S35	64471	control adj3 transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:06
S36	1465	(control adj3 transistor) (storage adj3 transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:06
S37	302	(control adj3 transistor) (storage adj3 transistor) vertical	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:06

EAST Search History

S38	28	(control adj3 transistor) (storage adj3 transistor) vertical (trench adj3 capacitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:47
S44	514	strap adj region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:50
S45	1151	strap adj2 region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:50
S46	1922	strap adj3 region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:50
S47	5202	strap adj10 region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:50
S48	5433	strap adj11 region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:50
S49	5643	strap adj12 region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:50
S50	6678	strap adj92 region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:50

EAST Search History

S51	6679	strap adj93 region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:50
S52	0	(strap or diffusion) adj2 region adj99 (below or lower or higher) adj99 ((strap or diffusion) adj2 region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:51
S53	724	((strap or diffusion) adj2 region) adj99 (below or lower or higher) adj99 ((strap or diffusion) adj2 region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:51
S54	514	((strap or diffusion) adj2 region) adj10 (below or lower or higher) adj10 ((strap or diffusion) adj2 region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:51
S55	493	((strap or diffusion) adj2 region) adj9 (below or lower or higher) adj9 ((strap or diffusion) adj2 region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:51
S56	450	((strap or diffusion) adj2 region) adj8 (below or lower or higher) adj8 ((strap or diffusion) adj2 region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:51
S57	381	((strap or diffusion) adj2 region) adj7 (below or lower or higher) adj7 ((strap or diffusion) adj2 region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:52
S58	293	((strap or diffusion) adj2 region) adj6 (below or lower or higher) adj6 ((strap or diffusion) adj2 region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:52

EAST Search History

S59	229	((strap or diffusion) adj2 region) adj5 (below or lower or higher) adj5 ((strap or diffusion) adj2 region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:52
S60	173	((strap or diffusion) adj2 region) adj4 (below or lower or higher) adj4 ((strap or diffusion) adj2 region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:52
S61	103	((strap or diffusion) adj2 region) adj3 (below or lower or higher) adj3 ((strap or diffusion) adj2 region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/05/04 08:41
S62	4	("6426252" or "20020076880").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 13:56
S63	2	((strap or diffusion) adj2 region) adj3 (below or lower or higher) adj3 ((strap or diffusion) adj2 region) (trench adj2 capacitor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 14:40
S64	87	(trench adj2 capacitor) (trench adj4 monocrystalline)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 15:05
S65	4	(trench adj2 capacitor) (trench adj3 filled adj4 monocrystalline)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/11/22 15:06
S66	221	8f2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 07:30

EAST Search History

S67	9	8f2 (control adj cell)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 07:31
S68	629	(buried adj2 (junction or strap)) (capacit\$4) (deep adj trench)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 10:08
S69	383	(buried adj2 (junction or strap)) ((deep adj trench) adj2 (capacit\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 10:08
S70	268	(buried adj2 (junction or strap)) ((deep adj trench) adj2 (capacit\$4)) (vertical)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 13:25
S71	9	(buried adj2 (junction or strap)) ((deep adj trench) adj2 (capacit\$4)) (vertical adj pass adj transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 10:09
S72	9	(buried adj2 (junction or strap)) ((deep adj trench) adj2 (capacit\$4)) (vertical adj pass adj transistor) control storage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 10:11
S73	1	((first second) adj buried adj2 (junction or strap)) ((deep adj trench) adj2 (capacit\$4)) (vertical adj pass adj transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 10:12
S74	1	((first second) adj buried adj2 (junction or strap)) (deep adj trench) (capacit\$4) (vertical adj pass adj transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 10:12

EAST Search History

S75	12	((first second) adj buried adj2 (junction or strap))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 10:13
S76	11	((first second) adj buried adj2 (junction or strap)) (deep adj trench)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 15:59
S77	1	((first second) adj buried adj2 (junction or strap)) (deep adj trench) control	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 10:16
S78	3	((first second) adj buried adj2 (junction or strap)) (deep adj trench) control\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 10:16
S79	43	vertical adj pass adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 10:53
S80	20	vertical adj pass adj transistor (threshold adj voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 10:47
S81	4	"6946696"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 10:47
S82	190	((storage control) adj node)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 10:53

EAST Search History

S83	81	((buried adj2 (junction or strap)) ((deep adj trench) adj2 (capacit\$4)) (vertical) (threshold adj voltage))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 13:29
S84	5	((first second) adj buried adj2 (junction or strap)) ((deep adj trench) adj2 (capacit\$4)) (vertical) (threshold adj voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 13:33
S85	14	"6399447"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 13:36
S86	4	("5670805" or "5360758").pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 14:49
S87	81	(257/220).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/10 15:00
S88	14	S87 (threshold adj voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 15:02
S91	12	((first second) adj buried adj2 (junction or strap))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/11 11:29
S92	1	((first second) adj buried adj2 (junction or strap)) ((floating conduct\$4) adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 16:01

EAST Search History

S96	3	((floating conduct\$4) adj region) (pinch-off or pinchoff or (pinch adj off))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 16:02
S97	152	(vertical adj2 transistor) (pinch-off or pinchoff or (pinch adj off))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/10 16:02
S98	41	(vertical adj2 transistor) (pinch-off or pinchoff or (pinch adj off)) (deep adj trench) (capacit\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/11 11:29
S99	25	((first second) adj2 buried adj2 (junction or strap))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/11 11:30
S100	12	((first second) adj2 buried adj2 (junction or strap)) (((pass or access) adj2 transistor) or (pass adj2 gate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/11 11:30
S101	12	((first second) adj2 buried adj2 (junction or strap)) (((pass or access) adj2 transistor) or (pass adj2 gate)) (deep adj2 trench)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/11 11:31
S102	12	((first second) adj2 buried adj2 (junction or strap)) (((pass or access) adj2 transistor) or (pass adj2 gate)) (deep adj2 trench) (capacit\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/01/11 11:34
S103	8	((first second) adj2 buried adj2 (junction or strap)) (((pass or access) adj2 transistor) or (pass adj2 gate)) (deep adj2 trench) (capacit\$4) (vertical)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/05/04 08:31